

Fig. 1

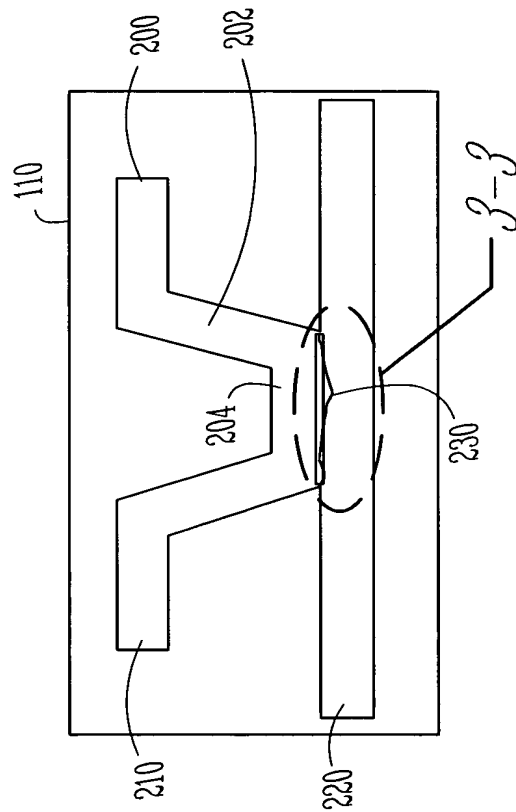
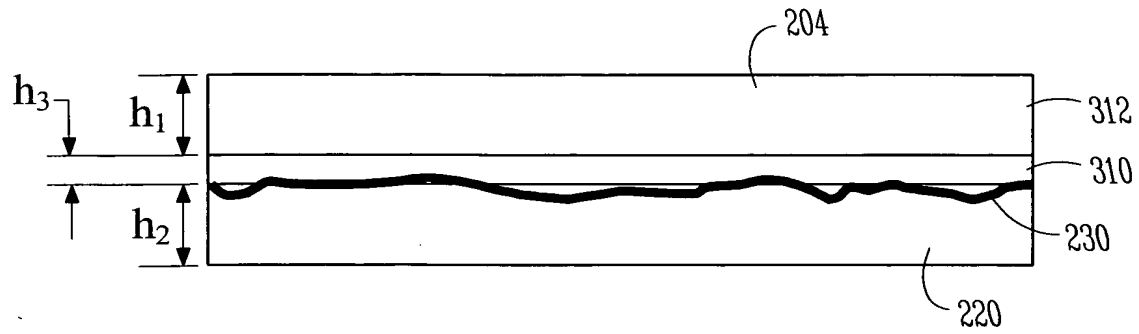
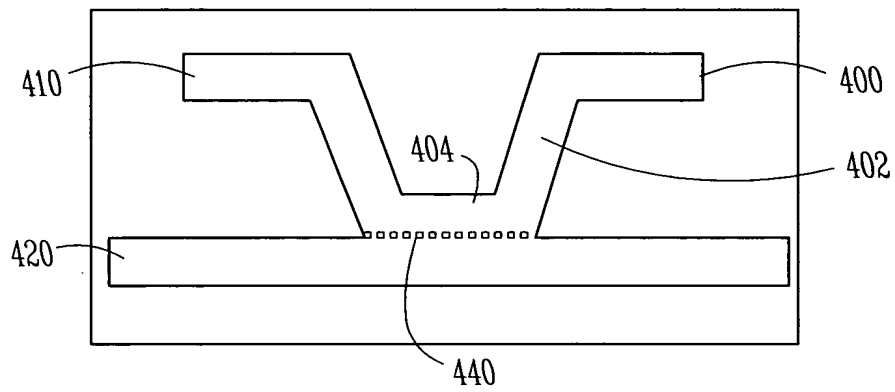


Fig. 2 (Prior Art)

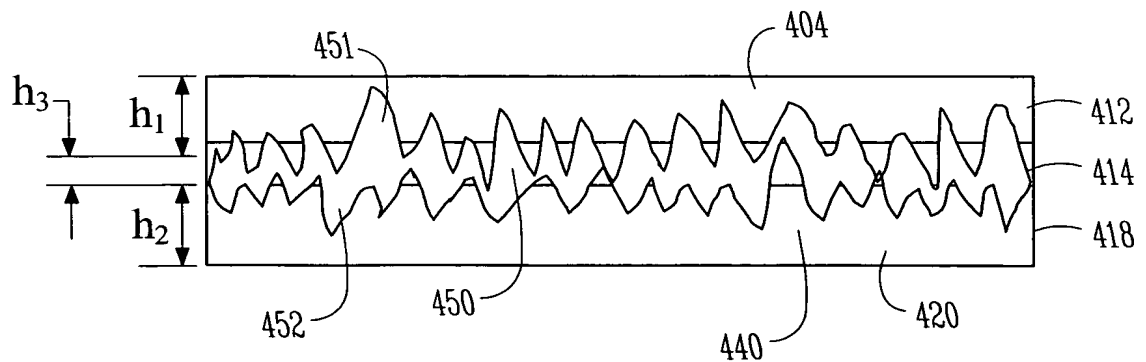
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*Fig. 3 (Prior Art)*



*Fig. 4A*



*Fig. 4B*

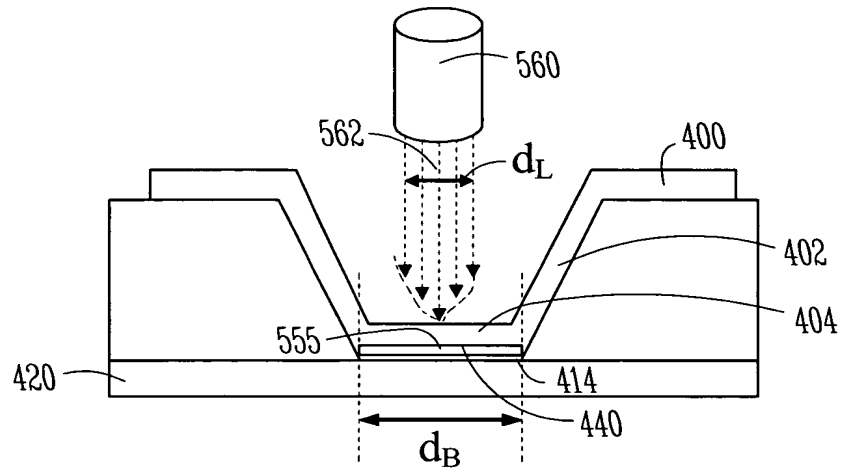
A cross-sectional view of a device. It shows a substrate 420 at the bottom. Above the substrate is a layer 510. Within layer 510, there is a V-shaped feature 520. The top surface of the right-hand side of the V-shaped feature is labeled 521.

This diagram shows a cross-sectional view of a semiconductor device with a central gap. On the left, a substrate 420 supports a layer 532. A sloped layer 511 is on top of 532, and a horizontal layer 551 is at the bottom of this section. On the right, a substrate 520 supports a layer 533. A sloped layer 521 is on top of 533, and a horizontal layer 550 is at the bottom of this section. The central gap contains a layer 551. Arrows indicate a flow or process from the top layers 532 and 533 towards the central gap. A dashed line 531 separates the left and right structures. A layer 404 is shown at the bottom of the central gap, and a layer 510 is shown on the right side of the gap.

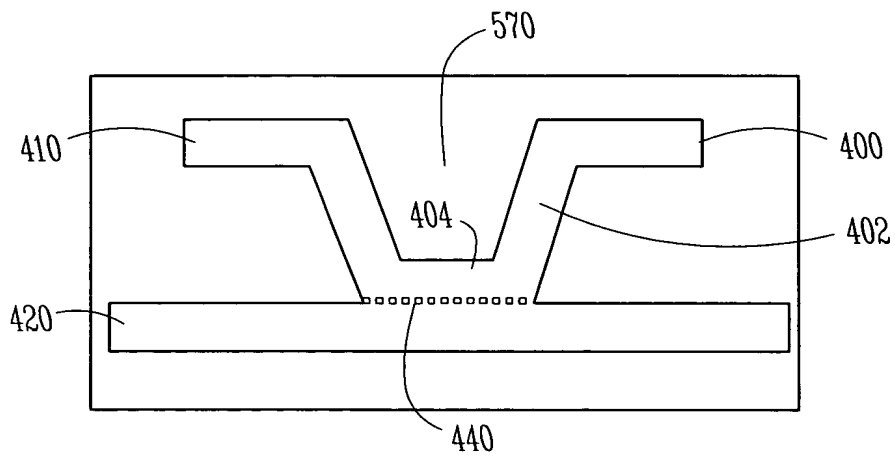
A cross-sectional view of a semiconductor device. A substrate 420 is shown at the bottom. A trench 400 is formed in the substrate. The trench has a bottom surface 412 and side walls 402. A layer 410 is deposited on the top surface of the substrate and the side walls of the trench. A layer 550 is deposited on the bottom surface of the trench. A layer 414 is deposited on the top surface of the substrate and the side walls of the trench, and is in contact with the layer 550.

*Fig. 5C*

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*Fig. 5D*



*Fig. 5E*

600

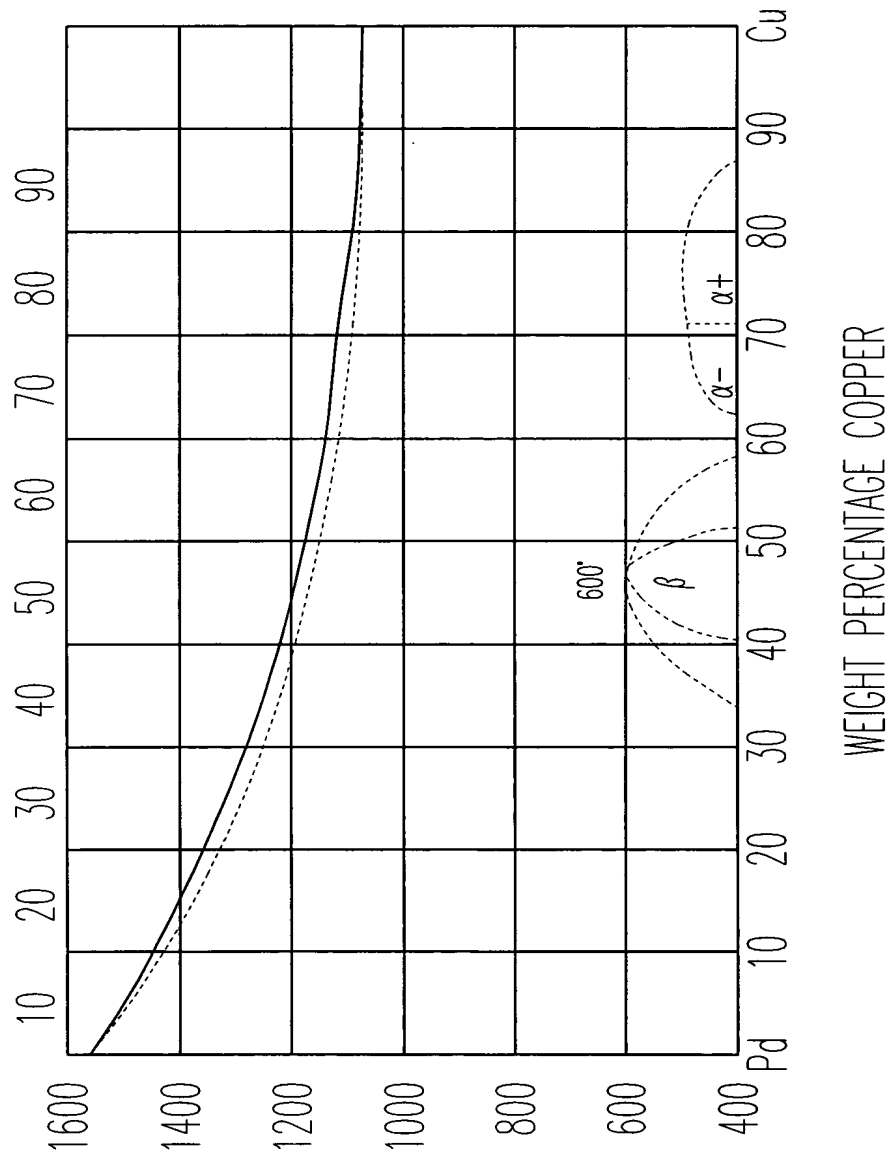
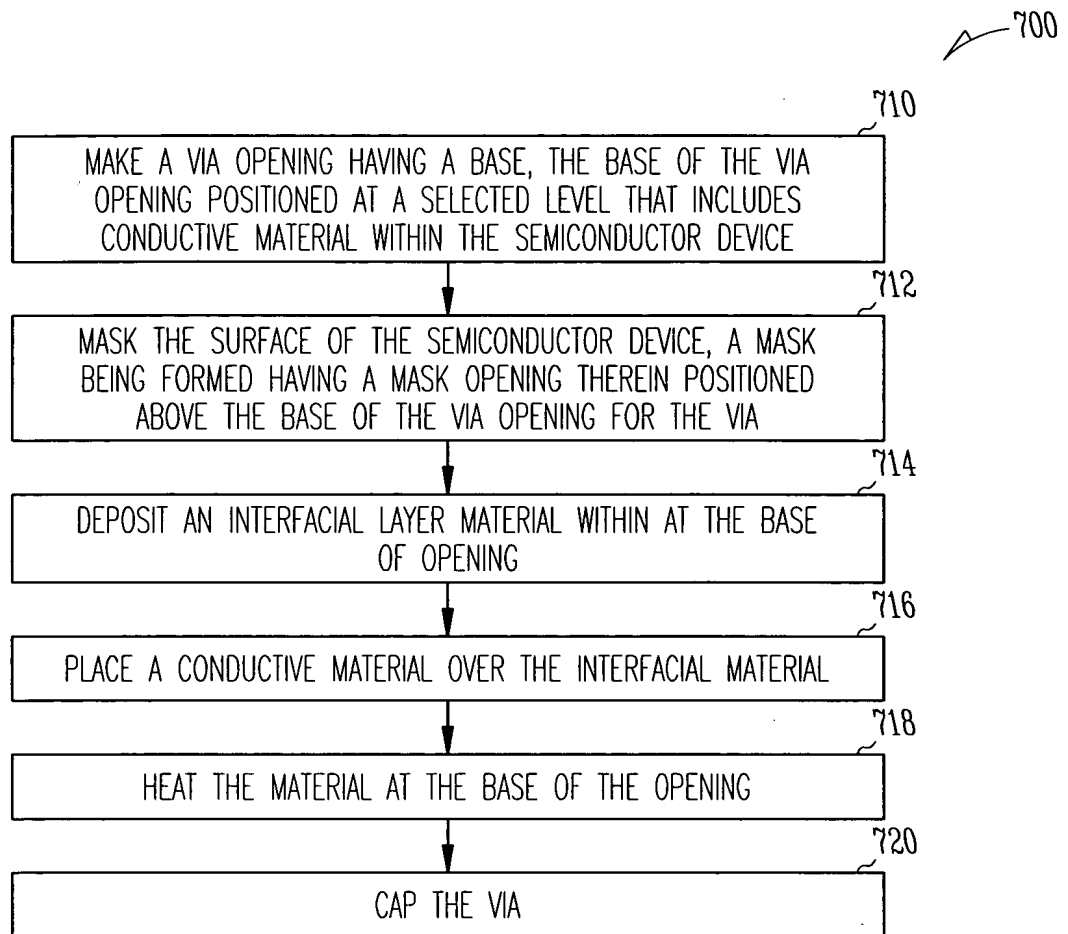
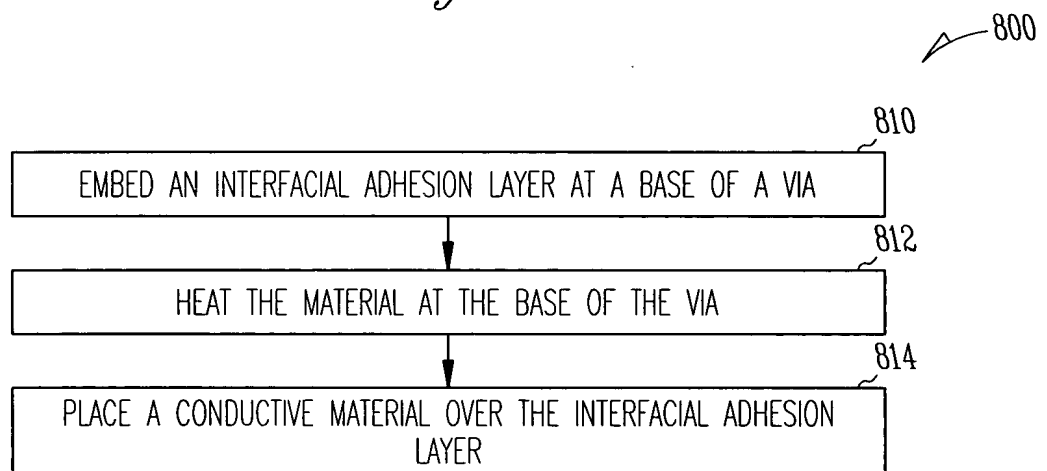


Fig. 6

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*Fig. 7*



*Fig. 8*